NSN 5961-01-084-2584

Transistor - Page 1 of 1

View Online at https://aerobasegroup.com/nsn/5961-01-084-2584

Inclosure Material:

Metal

Overall Length:

0.280 inches

Overall Diameter:

Between 0.300 inches and 0.370 inches

Mounting Facility Quantity:

1

Internal Configuration:

Junction contact

Mounting Method:

Threaded stud

Features Provided:

Hermetically sealed case

Thread Size:

0.164 inches

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

60.0 collector to emitter reverse voltage, with base short-circuited to emitter and 33.0 collector to emitter voltage/static/base open and 4.0 emitter to base voltage, static, collector open

Current Rating Per Characteristic:

0.50 amperes source cutoff current

Power Rating Per Characteristic:

5.8 watts small-signal input power, common-collector absolute

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius junction

Special Features:

Burn-in requirement, vce 7.0vdc, ic 0.4adc, 168 hours min duration; junction pattern arrangement: npn

Test Data Document:

99971-7536771 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Thread Series Designator:

Unc

Terminal Type And Quantity:

4 ribbon

Shelf Life:

N/a

Unit Of Measure:

--

Demilitarization:

No

Fiig:

A110a0